

AMENDMENT TO THE SPECIFICATION

Please amend the paragraph on page 14, lines 10 - 21 as follows:

Thereafter, as shown in Figs. 4(c) and 7, as the third PEP, an amorphous ITO film that is a transparent conductive film is formed, and then is etched by etching solution containing relatively mild acid such as oxalic acid using a resist mask. Thus, the ITO film 37 is formed. This ITO film 37 constitutes the pixel electrode for display, which is a pixel. In addition, in this embodiment, the ITO film 37 is provided at positions where the ITO film 37 covers the source and drain electrodes 35 and 36 37 and where the ITO film 37 covers the data line. Furthermore, when the ITO film 37 is formed by the resist mask, the Al pattern 41 which is not covered with the ITO film 37 is patterned. The source and drain electrodes 35 and 36 that are the upper electrodes are formed by this patterning, and an unnecessary portion of the Al pattern 41 on the gate line 32 is removed. As the result of this step, a structure that the ITO film 37 overlaps the upper electrodes and extends so as to constitute the pixel electrode is obtained.